PIN PHOTODIODES

InGaAs PIN Photodiodes

Part Number	OPTICAL AND ELECTRICAL CHARACTERISTICS (T_a = 25°C)					Package	Notes
	Active area dia. (μm)	η (%)	f_c (MHz)	I_D (nA)	C_t (pF)		
		V_R=1V λ=1300nm	R_L=50Ω, λ=1300nm −3dB from 500kHz V_R=5V	V_R=5V	f=1MHz V_R=5V		
FID13Z32TU	300	74 1*	500	0.5	5	TU	Lensed cap for fiber coupling modified TO-18
FID3Z1LX	50	81	3000	0.05	0.7	LX	With GI 50/125 micron MMF
FID3Z2KX	80	85	2000	0.1	0.9	KX	
FID3Z2LX	80	85	2000	0.1	0.9	LX	

InGaAs PIN Photodiodes for Analog Application

Part Number	Active area dia. (μm)	OPTICAL AND ELECTRICAL CHARACTERISTICS (T_a = 25°C)							Package	Notes
		R (A/W)	f_c (MHz)	I_D (nA)	C_t (pF)	IMD2 (dBc)	IMD3 (dBc)	ORL (dB)		
		V_R=1V λ=1300nm	R_L=50Ω, λ=1300nm −3dB from 500kHz V_R=5V	V_R=5V	f=1MHz V_R=5V	2LD, 2 tone OMD=70% each P_{in}=0dBm λ=1300nm V_R=5V f_1=244MHz f_2=250MHz 2*				
FID3S1HX	80	0.85	2000	0.1	0.9	-75 max.	-90 max.	40 min.	HX	With SMF
FID3S1KX	80	0.85	2000	0.1	0.9	-75 max.	-90 max.	40 min.	KX	With SMF

1* Actual value may vary due to user mechanical alignment procedures and/or receptacle and fiber tolerances. Our specified values are measured by coupling from GI 50/125 micron MMF.

2* Modulation input light signals are from two independent laser sources with modualtion frequency f_1=244MHz and f_2=250MHz respectively.

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